

CMLDM8005
SURFACE MOUNT SILICON
DUAL P-CHANNEL
ENHANCEMENT-MODE
MOSFET



SOT-563 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLDM8005 consists of dual P-Channel enhancement-mode silicon MOSFETs designed for high speed pulsed amplifier and driver applications. These MOSFETs offer very low $r_{DS(ON)}$ and low threshold voltage.

MARKING CODE: CC8

FEATURES:

- ESD protection up to 1800V (Human Body Model)
- 350mW power dissipation
- Very low $r_{DS(ON)}$
- Low threshold voltage
- Logic level compatible
- Small, SOT-563 surface mount package
- Complementary dual N-Channel device: CMLDM7005

APPLICATIONS:

- Load switch/Level shifting
- Battery charging
- Boost switch
- Electro-luminescent backlighting

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

| | |
|--|--|
| Drain-Source Voltage | |
| Gate-Source Voltage | |
| Continuous Drain Current (Steady State - Note 1) | |
| Continuous Source Current (Body Diode) | |
| Maximum Pulsed Drain Current | |
| Power Dissipation (Note 1) | |
| Power Dissipation (Note 2) | |
| Power Dissipation (Note 2) | |
| Operating and Storage Junction Temperature | |
| Thermal Resistance (Note 1) | |

| SYMBOL | | UNITS |
|----------------|-------------|--------------------|
| V_{DS} | 20 | V |
| V_{GS} | 8.0 | V |
| I_D | 650 | mA |
| I_S | 250 | mA |
| I_{DM} | 1.0 | A |
| P_D | 350 | mW |
| P_D | 300 | mW |
| P_D | 150 | mW |
| T_J, T_{stg} | -65 to +150 | $^\circ\text{C}$ |
| θ_{JA} | 357 | $^\circ\text{C/W}$ |

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|----------------------|--|-----|------|------|---------------|
| I_{GSSF}, I_{GSSR} | $V_{GS}=4.5\text{V}, V_{DS}=0$ | | | 10 | μA |
| I_{DSS} | $V_{DS}=16\text{V}, V_{GS}=0$ | | | 100 | nA |
| BV_{DSS} | $V_{GS}=0, I_D=250\mu\text{A}$ | 20 | | | V |
| $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu\text{A}$ | 0.5 | | 1.0 | V |
| V_{SD} | $V_{GS}=0, I_S=250\text{mA}$ | | | 1.1 | V |
| $r_{DS(ON)}$ | $V_{GS}=4.5\text{V}, I_D=350\text{mA}$ | | 0.25 | 0.36 | Ω |
| $r_{DS(ON)}$ | $V_{GS}=2.5\text{V}, I_D=300\text{mA}$ | | 0.37 | 0.5 | Ω |
| $r_{DS(ON)}$ | $V_{GS}=1.8\text{V}, I_D=150\text{mA}$ | | | 0.8 | Ω |

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm²
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm²
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm²

R6 (8-June 2015)

CMLDM8005

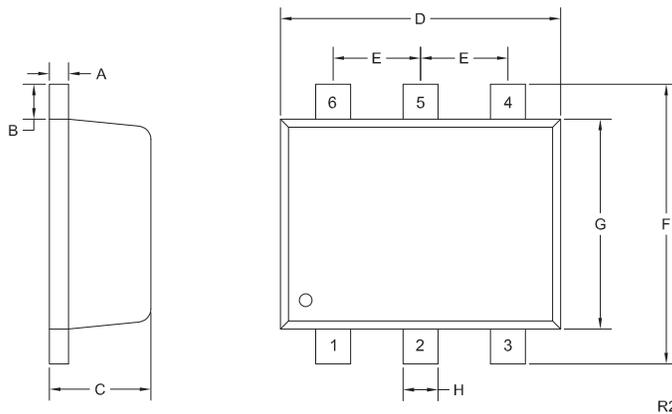
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ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | TYP | UNITS |
|---------------------|---|-----|------|-------|
| g_{FS} | $V_{DS}=10\text{V}, I_D=200\text{mA}$ | 0.2 | | S |
| C_{rSS} | $V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$ | | 25 | pF |
| C_{iss} | $V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$ | | 100 | pF |
| C_{oss} | $V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$ | | 21 | pF |
| $Q_{g(\text{tot})}$ | $V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$ | | 1.2 | nC |
| Q_{gs} | $V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$ | | 0.24 | nC |
| Q_{gd} | $V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$ | | 0.36 | nC |
| t_{on} | $V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}, R_G=10\Omega$ | | 38 | ns |
| t_{off} | $V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}, R_G=10\Omega$ | | 48 | ns |

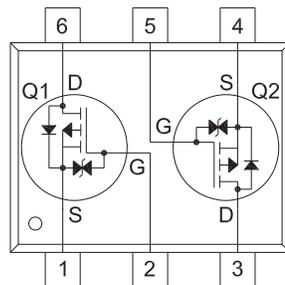
SOT-563 CASE - MECHANICAL OUTLINE



| SYMBOL | DIMENSIONS | | | |
|--------|------------|-------|-------------|------|
| | INCHES | | MILLIMETERS | |
| | MIN | MAX | MIN | MAX |
| A | 0.0027 | 0.007 | 0.07 | 0.18 |
| B | 0.008 | | 0.20 | |
| C | 0.017 | 0.024 | 0.45 | 0.60 |
| D | 0.059 | 0.067 | 1.50 | 1.70 |
| E | 0.020 | | 0.50 | |
| F | 0.059 | 0.067 | 1.50 | 1.70 |
| G | 0.043 | 0.051 | 1.10 | 1.30 |
| H | 0.006 | 0.012 | 0.15 | 0.30 |

SOT-563 (REV: R2)

PIN CONFIGURATION



LEAD CODE:

- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2
- 6) Drain Q1

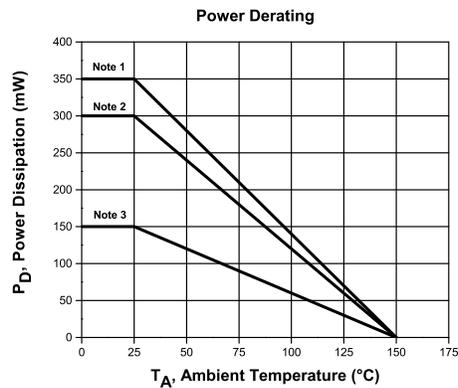
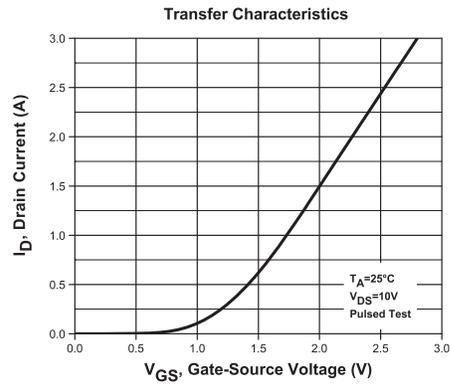
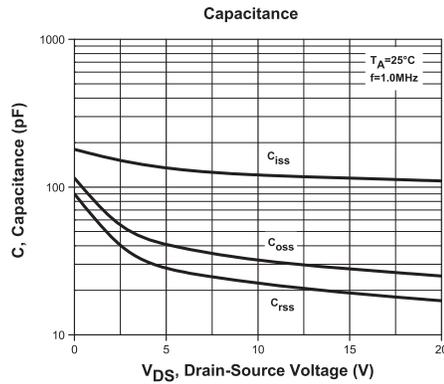
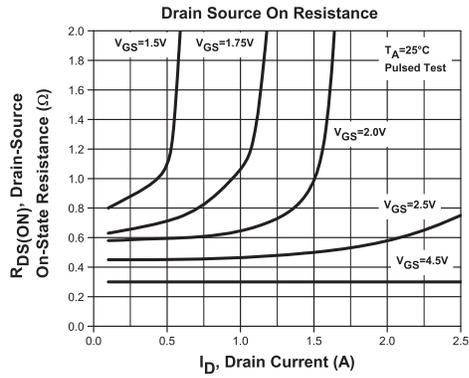
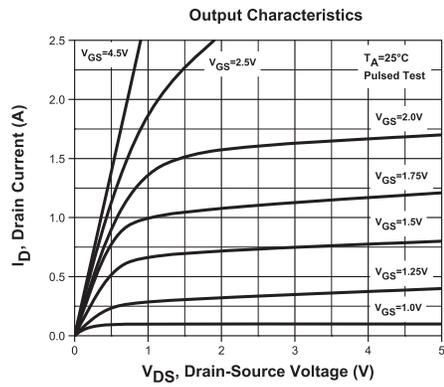
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TYPICAL ELECTRICAL CHARACTERISTICS



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SERVICES

- Bonded Inventory
- Custom Electrical Screening
- Custom Electrical Characteristic Curves
- SPICE Models
- Custom Packaging
- Package Base Options
- Custom Device Development/ Multi Discrete Modules (MDM™)
- Bare Die Available for Hybrid Applications

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